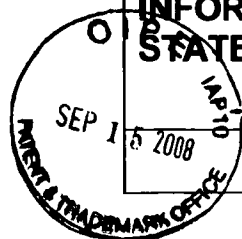


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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Application Number	10/775,999
Filing Date	February 10, 2004
First Named Inventor	Faris
Group Art Unit	1792
Examiner Name	Binh X. Tran
Attorney Docket Number	Reveo-0179

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		4,371,421	01-Feb-83	Fan et al.	156	624	
		4,471,003	11-Sep-84	Cann	427	34	
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		4,585,945	29-Apr-86	Bruel et al.	250	492.2	
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		4,846,931	11-Jul-89	Gmitter et al.	156	633	
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		5,273,616	28-Dec-93	Bozler et al.	156	603	
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		5,374,564	20-Dec-94	Bruel	437	24	
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		6,137,110	24-Oct-00	Pellin et al.	250	423	
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Examiner Signature	/Binh Tran/	Date Considered	11/14/2008
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/BT/							

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						YES	NO
/BT/	EP0355913A1	28-Feb-90	Europe				
↓	WO 95/20824A1	3-Aug-95	PCT				
	WO 98/20543A2	14-May-98	PCT				
	WO 98/33209	30-Jul-98	PCT				
	WO 99/05711A1	4-Feb-99	PCT				
	WO 99/08316A1	18-Feb-99	PCT				
	WO 99/35674A1	15-Jul-99	PCT				
	WO 99/39377A1	5-Aug-99	PCT				
	WO 99/66559A1	23-Dec-99	PCT				
	WO 00/03429A1	20-Jan-00	PCT				X
	WO 00/24059A1	27-Apr-00	PCT				X
	WO 00/24054A1	27-Apr-00	PCT				X
	WO 00/46847A1	10-Aug-00	PCT				
	WO 00/48238A1	17-Aug-00	PCT				
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Examiner Signature	/Binh Tran/	Date Considered	11/14/2008
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Sheet 6 of 8	Attorney Docket Number	Reveo-0179

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/775,999
	Filing Date	February 10, 2004
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	Examiner Name	Binh X. Tran
Sheet 8 of 8	Attorney Docket Number	Reveo-0179

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